

isc Silicon PNP Darlington Power Transistor

2N6036

DESCRIPTION

- Collector–Emitter Sustaining Voltage—
: $V_{CEO(SUS)} = -80V(\text{Min.})$
- DC Current Gain—
: $h_{FE} = 750(\text{Min}) @ I_C = -2A$
- Complement to Type 2N6039
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

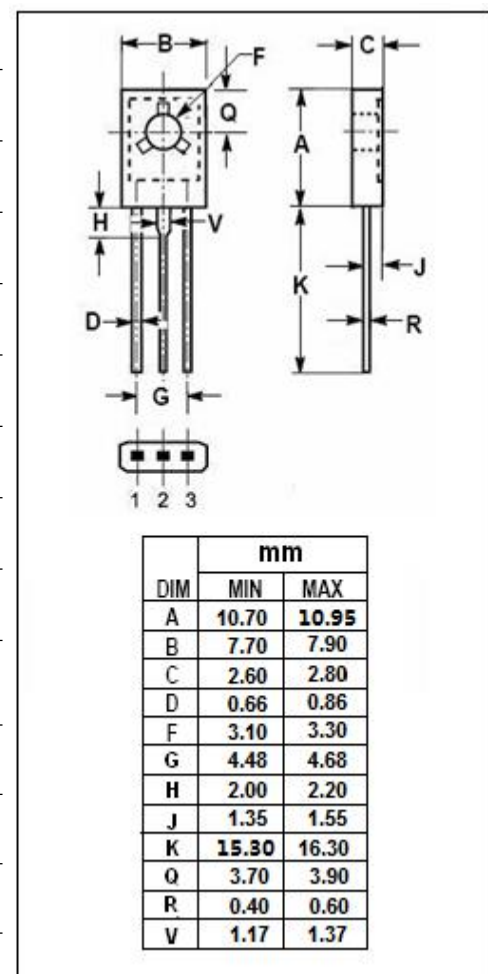
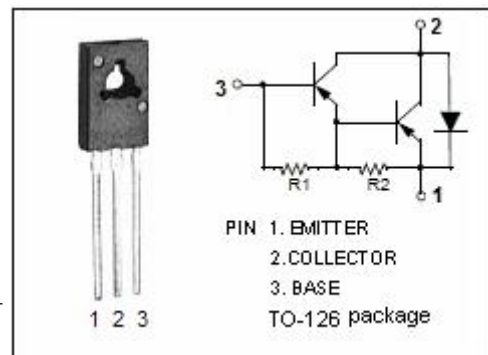
- Designed for general-purpose amplifier and low-speed switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-8	A
I_B	Base Current	-0.1	A
P_C	Collector Power Dissipation $T_C=25^\circ\text{C}$	40	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.12	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	83.3	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -10\text{mA}$; $I_B = 0$	-80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}$; $I_B = -8\text{mA}$		-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}$; $I_B = -40\text{mA}$		-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -4\text{A}$; $I_B = -40\text{mA}$		-4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -2\text{A}$; $V_{CE} = -3\text{V}$		-2.8	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -80\text{V}$; $I_B = 0$		-0.1	mA
I_{CEX}	Collector Cutoff Current	$V_{CE} = -80\text{V}$; $V_{BE(off)} = -1.5\text{V}$; $V_{CB} = -80\text{V}$; $V_{BE(off)} = -1.5\text{V}$; $T_C = 125^{\circ}\text{C}$		-0.1 -0.5	mA
I_{CBO}	Collector Cutoff Current	$V_{CB} = -80\text{V}$; $I_E = 0$		-0.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$		-2.0	mA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}$; $V_{CE} = -3\text{V}$	500		
h_{FE-2}	DC Current Gain	$I_C = -2\text{A}$; $V_{CE} = -3\text{V}$	750	15000	
h_{FE-3}	DC Current Gain	$I_C = -4\text{A}$; $V_{CE} = -3\text{V}$	100		
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$; $f = 0.1\text{MHz}$		200	pF

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